

SANYO SEMICONDUCTOR 2SD904

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NPN Triple Diffused Mesa Type Silicon Transistor
For Horizontal Deflection Output of 20" Color TV
(With Damper Diode)

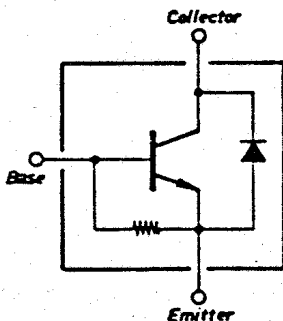
Absolute Maximum Ratings at Ta=25°C

Collector to Base Voltage	VCBO	1500	V
Collector to Emitter Voltage	VCEO	600	V
Emitter to Base Voltage	VEBO	6	V
Collector Current	IC	7	A
Collector Current (Peak)	icp	10	A
Collector Dissipation	PC	3	W
	PC	50	W
		Tc=25°C	
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-40~+150	°C

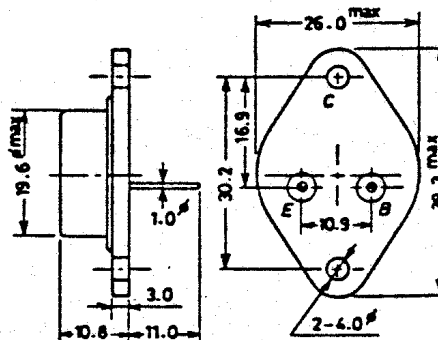
Electrical Characteristics at Ta=25°C

			min	typ	max	unit
Collector Cut off Current	ICES	VCB=1500V, VEB=0			1.0	mA
Emitter Cut off Current	IEBO	VEB=4V, IC=0	44		100	mA
Base to Emitter Voltage	VBE0	IE=200mA, IC=0	6.0			V
Emitter to Collector Voltage	VECO	IE=4A, IB=0			2.0	V
DC Current Gain	hFE (1)	VCE=5V, IC=4A	5		10	
	hFE (2)	VCE=5V, IC=1A	8			
C-E Saturation Voltage	VCE(sat)	IC=3A, IB=0.75A			5	V
B-E Saturation Voltage	VBE(sat)	IC=3A, IB=0.6A			1.6	V
C-E Sustain Voltage	VCE(sus)	IC=100mA, IB=0, L=35mH	600			
Fall Time	tf	IC=3A, IB=0.6A, Tc=80°C			1.0	µs

Equivalent Circuit



Case Outline (unit:mm)



EIAJ : TC-3, TB-3 C: Collector
JEDEC: TO-3 E: Emitter
 B: Base